

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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C3D03060F Silicon Carbide Schottky Diode Z-REC® RECTIFIER (Full-Pak)

 \mathbf{V}_{RRM} = 600 V $\mathbf{I}_{F}(\mathbf{T}_{c}=110^{\circ}\mathbf{C})$ = 3 A \mathbf{Q}_{c} = 6.7 nC

Features

- 600-Volt Schottky Rectifier
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on V_E

Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters

Package

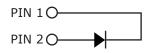






TO-220-F2





Part Number	Package	Marking		
C3D03060F	TO-220-F2	C3D03060		

Maximum Ratings (T_c = 25 °C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V _{RRM}	Repetitive Peak Reverse Voltage	600	V		
V _{RSM}	Surge Peak Reverse Voltage	600	V		
V _{DC}	DC Blocking Voltage	600	V		
I _F	Continuous Forward Current	5 3 2	А	T _c =25°C T _c =112°C T _c =135°C	Fig. 3
\mathbf{I}_{FRM}	Repetitive Peak Forward Surge Current	20 15	Α	T_c =25°C, t_p =10 mS, Half Sine Wave D=0.3 T_c =110°C, t_p =10 mS, Half Sine Wave D=0.3	
\mathbf{I}_{FSM}	Non-Repetitive Peak Forward Surge Current	28 22	А	T_c =25°C, t_p =10 mS, Half Sine Wave D=0.3 T_c =110°C, t_p =10 mS, Half Sine Wave D=0.3	
I_{FSM}	Non-Repetitive Peak Forward Surge Current	100	Α	T_c =25°C, t_p =10 μ S, Pulse	
P _{tot}	Power Dissipation	12.5 5.4	W	T _c =25°C T _c =110°C	Fig. 4
dV/dt	Diode dV/dt ruggedness	200	V/ns	V _R =0-600V	
T _J , T _{stg}	Operating Junction and Storage Temperature	-55 to +175	°C		
	TO-220 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	



Electrical Characteristics

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
V _F	Forward Voltage	1.5 1.8	1.7 2.4	V	$I_F = 3 \text{ A } T_J = 25^{\circ}\text{C}$ $I_F = 3 \text{ A } T_J = 175^{\circ}\text{C}$	Fig. 1
I_R	Reverse Current	4 8	20 80	μΑ	$V_R = 600 \text{ V } T_J = 25^{\circ}\text{C}$ $V_R = 600 \text{ V } T_J = 175^{\circ}\text{C}$	Fig. 2
Q _c	Total Capacitive Charge	7.6		nC	$V_R = 400 \text{ V, } I_F = 3A$ $di/dt = 500 \text{ A/}\mu\text{S}$ $T_J = 25^{\circ}\text{C}$	Fig. 5
С	Total Capacitance	166 14 11		pF	$V_R = 0 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$ $V_R = 200 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$ $V_R = 400 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$	Fig. 6
E _c	Capacitance Stored Energy	1.1		μJ	V _R = 400 V	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Тур.	Unit	Note
$R_{_{ heta JC}}$	Thermal Resistance from Junction to Case	12	°C/W	Fig. 8

Typical Performance

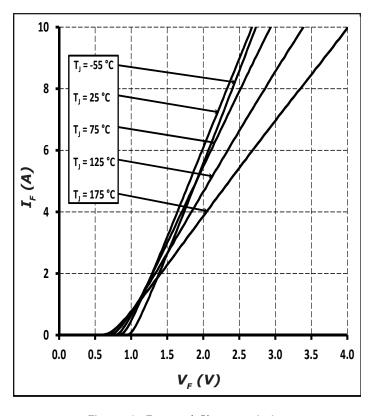


Figure 1. Forward Characteristics

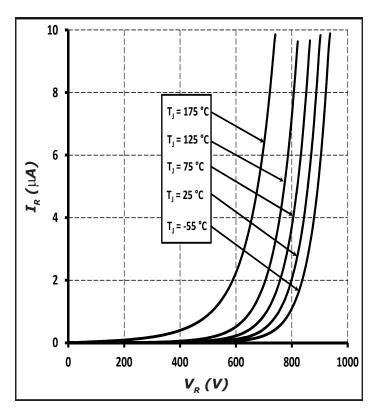
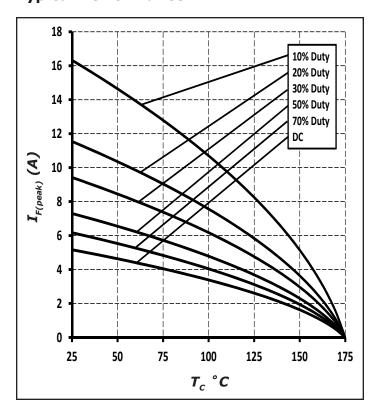


Figure 2. Reverse Characteristics



Typical Performance



 $P_{Tot}\left(W\right)$ T_c $^{\circ}C$

Figure 3. Current Derating

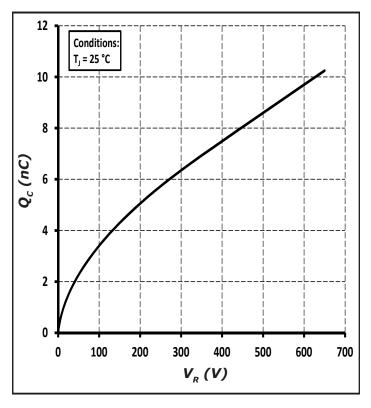


Figure 5. Total Capacitance Charge vs. Reverse Voltage

Figure 4. Power Derating

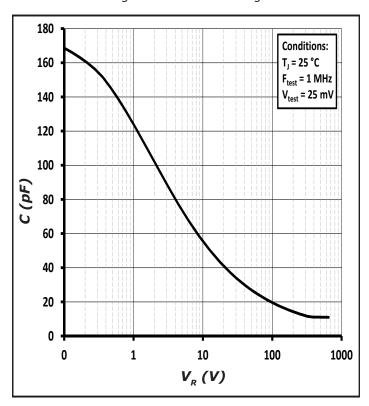


Figure 6. Capacitance vs. Reverse Voltage



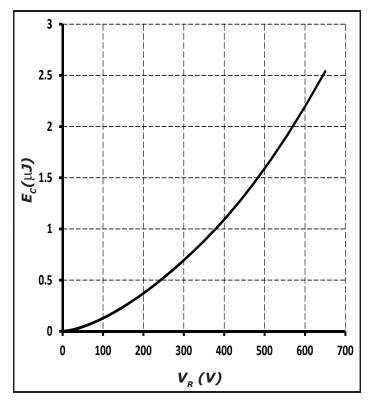


Figure 7. Capacitance Stored Energy

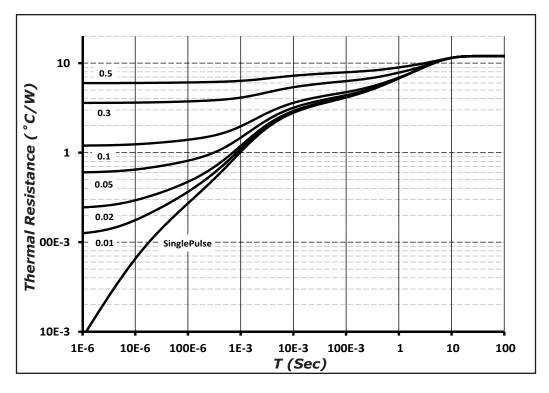
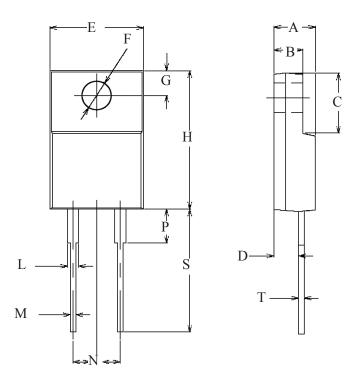


Figure 8. Transient Thermal Impedance



Package Dimensions

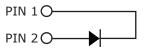
Package TO-220-F2



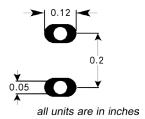
POS	Inc	hes	Millimeters		
P05	Min	Max	Min	Max	
А	0.177	0.194	4.5	4.93	
В	0.092	0.108	2.34	2.74	
С	0.256	0.272	6.5	6.9	
D	0.098	0.117	2.5	2.96	
E	0.39	0.408	9.9	10.36	
F	0.117	0.134	2.98	3.4	
G	0.122	0.138	3.1	3.5	
Н	0.617	0.633	15.67	16.07	
L	0.039	0.055	1	1.4	
М	0.016	0.036	0.4	0.91	
N	0.200 TYP		5.08 TYP		
Р	0.114	0.154	1.9	3.9	
S	0.476	0.519	12.1	13.18	
Т	0.016	0.031	0.4	0.8	

NOTE:

1. Dimension L, M, T apply for Solder Dip Finish



Recommended Solder Pad Layout



TO-220-2

Part Number	Package	Marking		
C3D03060F	TO-220-F2	C3D03060		





Diode Model

$$\begin{array}{c|c} & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & \\ & & & \\ & \\ & & \\ & & \\ & & \\ & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ &$$

$$Vf_T = V_T + If * R_T$$

$$V_T = 0.96 + (T_J^* - 1.1^*10^{-3})$$

 $R_T = 0.145 + (T_J^* 9.5^*10^{-4})$

Note: T_j = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C

Notes

• RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented January 2, 2013. RoHS Declarations for this product can be obtained from your Wolfpseed representative or from the Product Ecology section of our website at http://www.wolfspeed.com/Power/Tools-and-Support/Product-Ecology.

REACh Compliance

REACh substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a Cree representative to insure you get the most up-to-date REACh SVHC Declaration. REACh banned substance information (REACh Article 67) is also available upon request.

This product has not been designed or tested for use in, and is not intended for use in, applications implanted into
the human body nor in applications in which failure of the product could lead to death, personal injury or property
damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines,
cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control
systems, or air traffic control systems.

Related Links

- Cree SiC Schottky diode portfolio: http://www.wolfspeed.com/Power/Products#SiCSchottkyDiodes
- Schottky diode Spice models: http://www.wolfspeed.com/power/tools-and-support/DIODE-model-request2
- SiC MOSFET and diode reference designs: http://go.pardot.com/l/101562/2015-07-31/349i